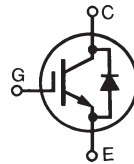


High Voltage, High Gain BiMOSFET™

IXBK55N300 IXBX55N300

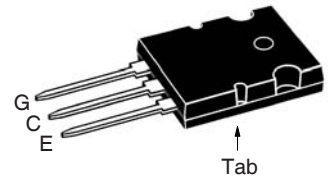
$V_{CES} = 3000V$
 $I_{C110} = 55A$
 $V_{CE(sat)} \leq 3.2V$

Monolithic Bipolar MOS Transistor

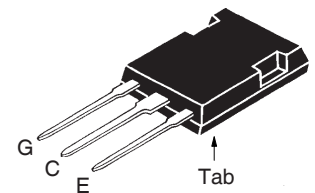


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	3000	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	3000	V
V_{GES}	Continuous	± 25	V
V_{GEM}	Transient	± 35	V
I_{C25}	$T_C = 25^\circ C$ (Chip Capability)	130	A
I_{LRMS}	$T_C = 25^\circ C$ (Lead RMS Limit)	120	A
I_{C110}	$T_C = 110^\circ C$	55	A
I_{CM}	$T_C = 25^\circ C$, 1ms	600	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 2\Omega$ Clamped Inductive Load	$I_{CM} = 110$ @ $0.8 \cdot V_{CES}$	A
T_{SC} (SCSOA)	$V_{GE} = 15V$, $T_J = 125^\circ C$, $R_G = 10\Omega$, $V_{CE} = 1250V$, Non-Repetitive	10	μs
P_C	$T_C = 25^\circ C$	625	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L T_{SOLD}	Maximum Lead Temperature for Soldering 1.6 mm (0.062 in.) from Case for 10	300 260	$^\circ C$ $^\circ C$
M_d F_C	Mounting Torque (TO-264) Mounting Force (PLUS247)	1.13/10 20..120/4.5..27	Nm/lb.in. N/lb.
Weight	TO-264 PLUS247	10 6	g g

TO-264 (IXBK)



PLUS247 (IXBX)



G = Gate E = Emitter
 C = Collector Tab = Collector

Features

- High Blocking Voltage
- International Standard Packages
- Low Conduction Losses
- High Current Handling Capability
- MOS Gate Turn-On
- Drive Simplicity

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Uninterruptible Power Supplies (UPS)
- Switch-Mode and Resonant-Mode Power Supplies
- Capacitor Discharge Circuits
- Laser Generators

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 1mA$, $V_{GE} = 0V$	3000		V
$V_{GE(th)}$	$I_C = 4mA$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			50 μA 3 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 25V$			± 200 nA
$V_{CE(sat)}$	$I_C = 55A$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$	2.7 3.3	3.2	V V

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

		Min.	Typ.	Max.	
g_{fs}	$I_C = 55\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	32	50		S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		7300		pF
C_{oes}			275		pF
C_{res}			83		pF
Q_g	$I_C = 55\text{A}, V_{GE} = 15\text{V}, V_{CE} = 1000\text{V}$		335		nC
Q_{ge}			47		nC
Q_{gc}			130		nC
$t_{d(on)}$	Resistive Switching Times, $T_J = 25^\circ\text{C}$ $I_C = 110\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 1250\text{V}, R_G = 2\Omega$		54		ns
t_r			307		ns
$t_{d(off)}$			230		ns
t_f			268		ns
$t_{d(on)}$	Resistive Switching Times, $T_J = 125^\circ\text{C}$ $I_C = 110\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 1250\text{V}, R_G = 2\Omega$		52		ns
t_r			585		ns
$t_{d(off)}$			215		ns
t_f			260		ns
R_{thJC}				0.20	$^\circ\text{C/W}$
R_{thCS}		0.15			$^\circ\text{C/W}$

Reverse Diode

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

		Min.	Typ.	Max	
V_F	$I_F = 55\text{A}, V_{GE} = 0\text{V}, \text{Note 1}$			2.5	V
t_{rr}	$I_F = 28\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$		1.9		μs
I_{RM}		$V_R = 100\text{V}, V_{GE} = 0\text{V}$		54	

Note 1: Pulse Test, $t \leq 300\mu\text{s}$, Duty Cycle, $d \leq 2\%$.

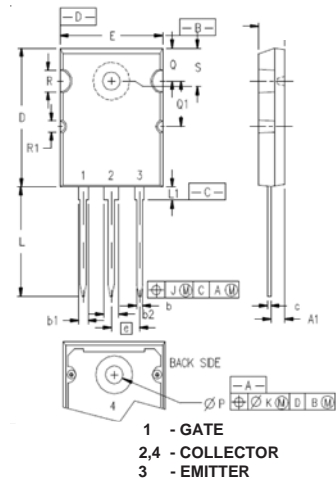
Additional provisions for lead-to-lead isolation are required at $V_{CE} > 1200\text{V}$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

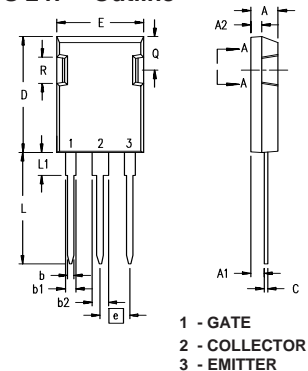
4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

TO-264 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

PLUS 247™ Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

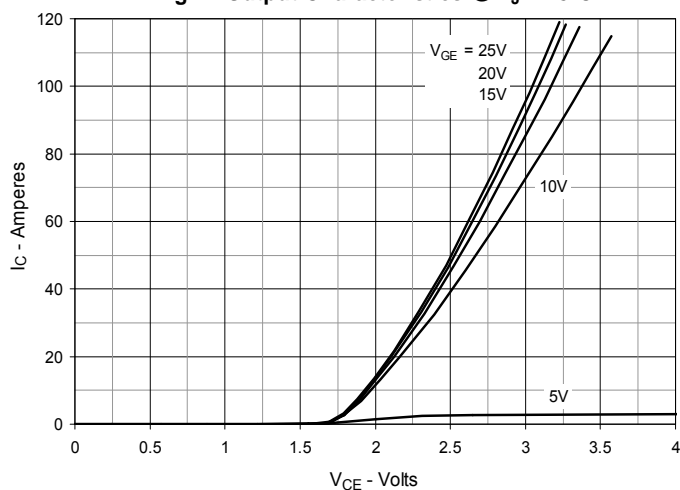
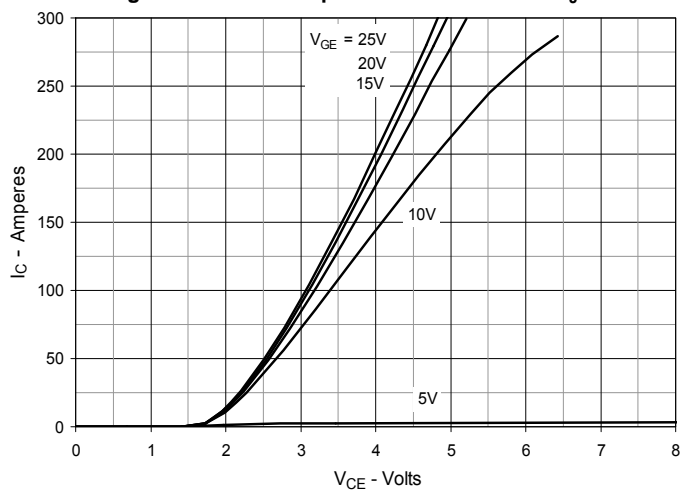
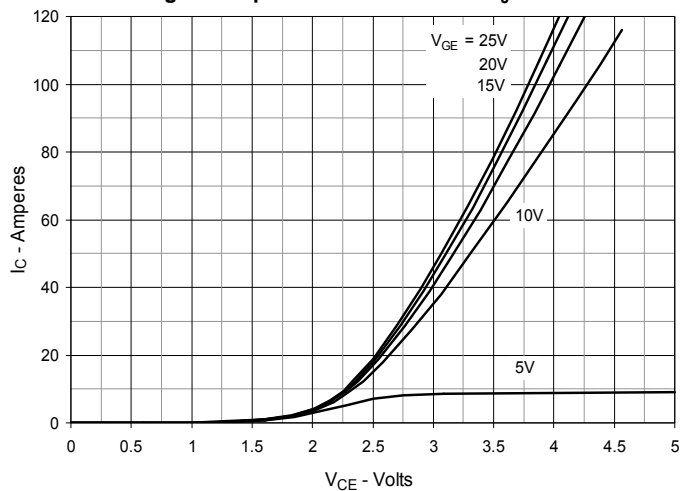
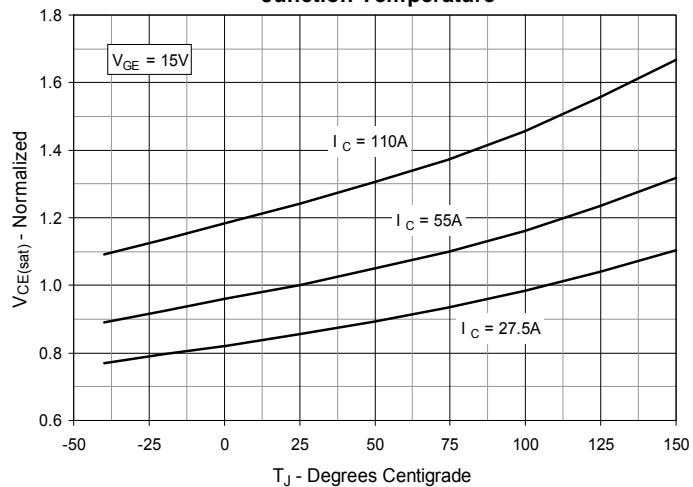
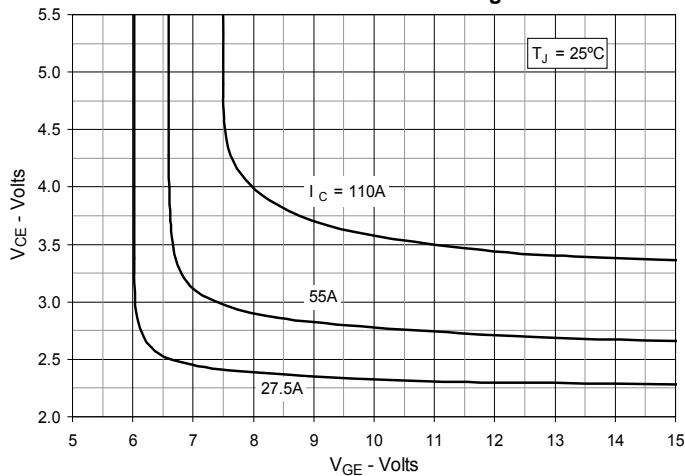
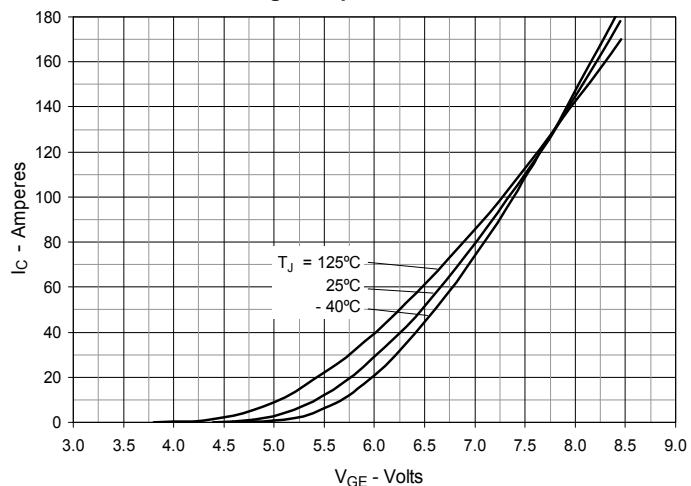
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


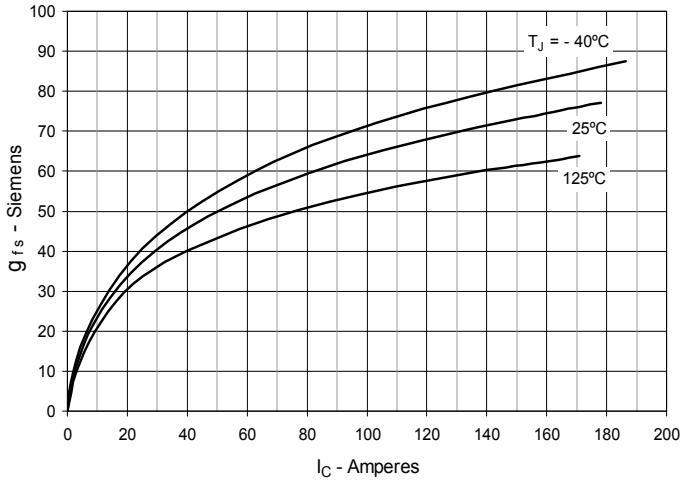
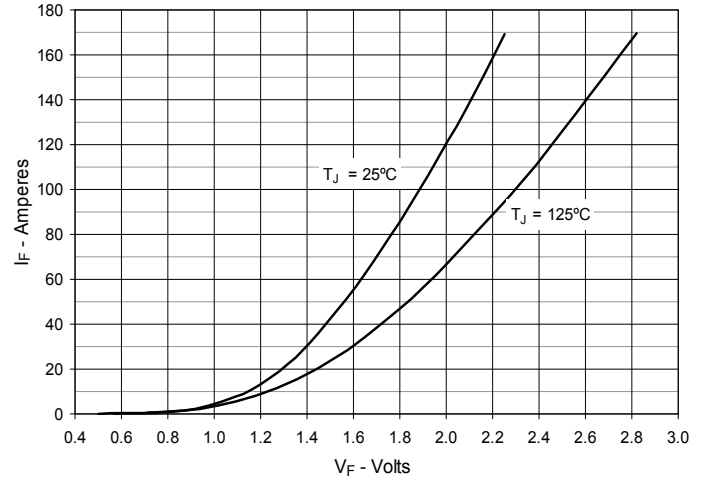
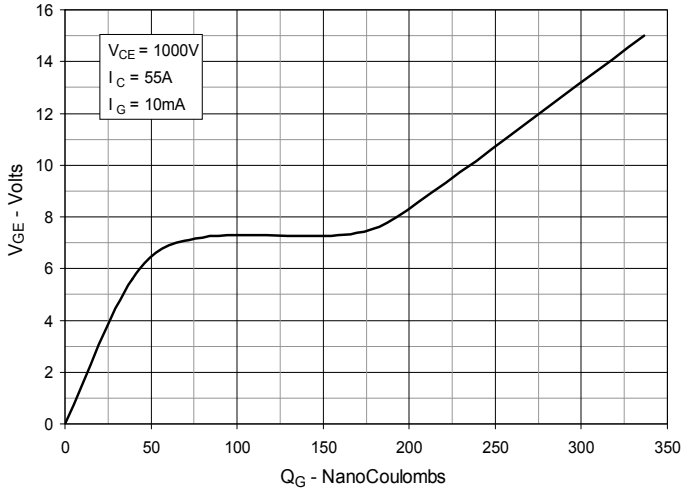
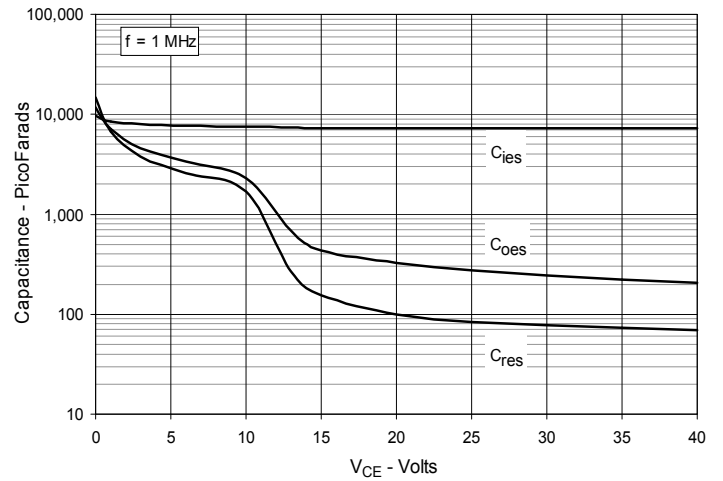
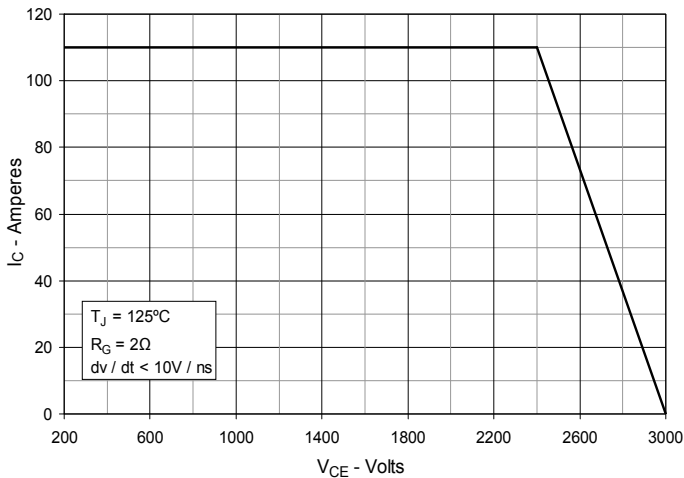
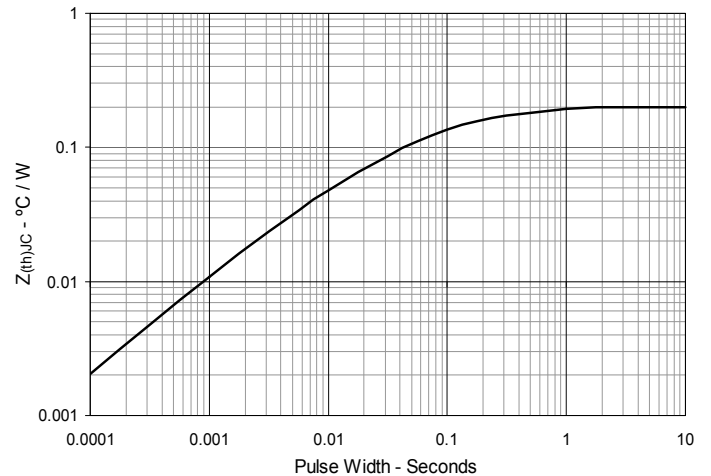
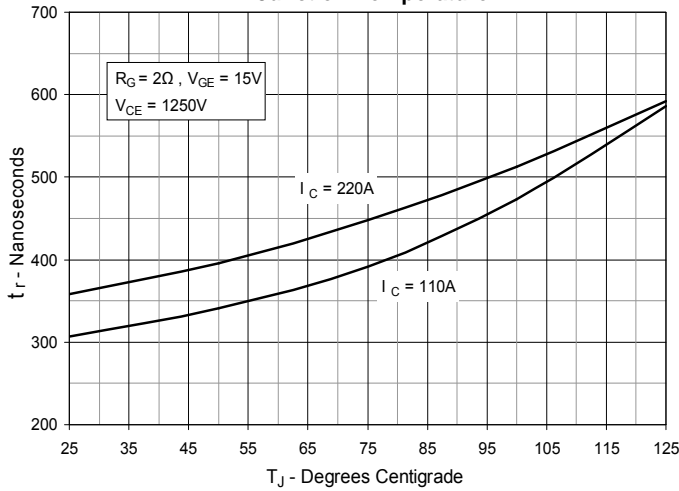
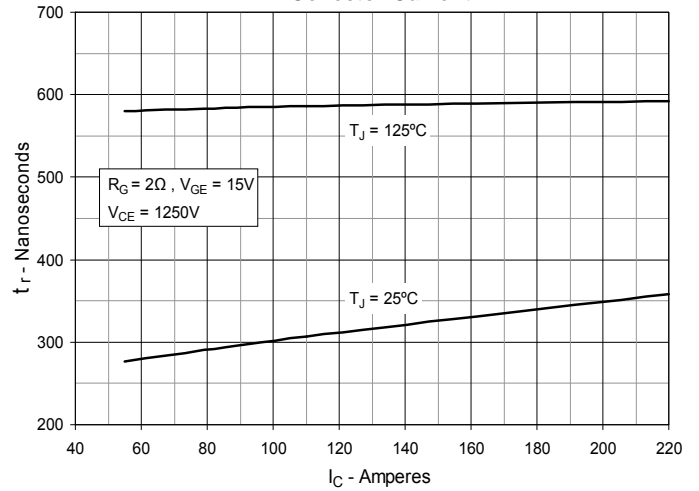
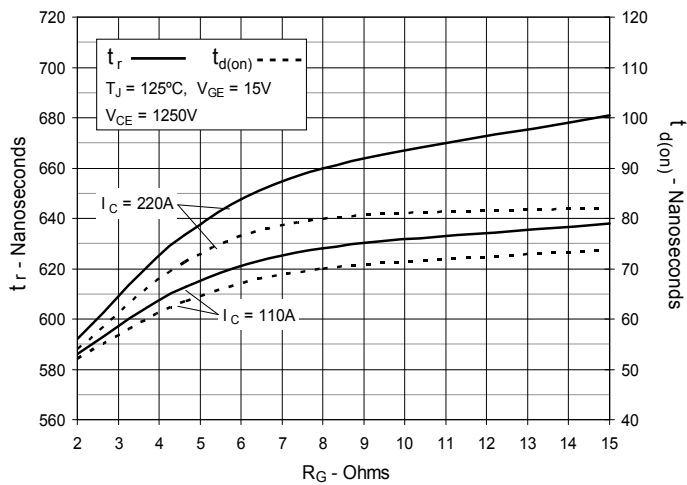
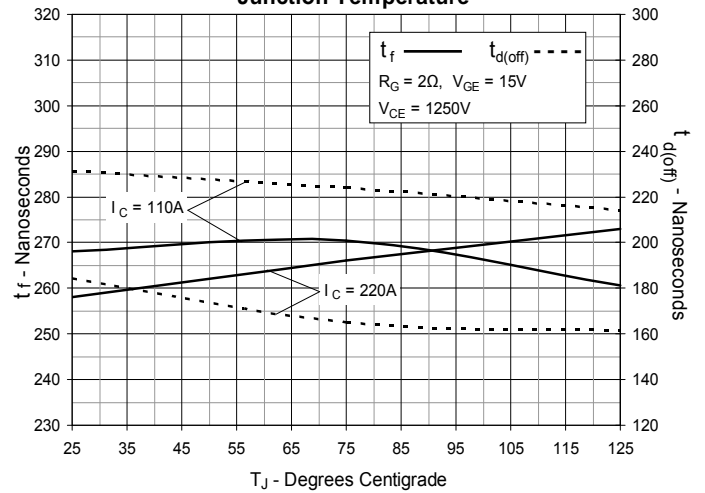
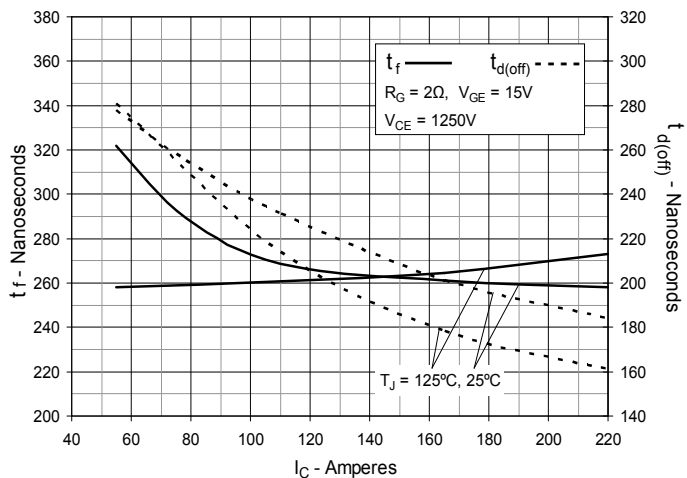
Fig. 7. Transconductance

Fig. 8. Forward Voltage Drop of Intrinsic Diode

Fig. 9. Gate Charge

Fig. 10. Capacitance

Fig. 11. Reverse-Bias Safe Operating Area

Fig. 12. Maximum Transient Thermal Impedance


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

Fig. 14. Resistive Turn-on Rise Time vs. Collector Current

Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

Fig. 17. Resistive Turn-off Switching Times vs. Collector Current

Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance
